

L Number	Hits	Search Text	DB	Time stamp
17	38	((treat\$4 heat\$3) with (dielectric insulat\$3) with (hard\$4 adj1 (layer film))).bi.	USPAT; US-PGPUB	2004/11/04 08:59
18	19	(treat\$4 with (dielectric insulat\$3) with (hard\$4 adj1 (layer film))).bi.	USPAT; US-PGPUB	2004/11/04 08:59
19	19	((treat\$4 heat\$3) with (dielectric insulat\$3) with (hard\$4 adj1 (layer film))).bi.) not ((treat\$4 with (dielectric insulat\$3) with (hard\$4 adj1 (layer film))).bi.)	USPAT; US-PGPUB	2004/11/04 09:40
20	3	((("6114259") or ("6054379") or ("5691238")).PN.	USPAT; US-PGPUB	2004/11/04 09:41
-	71	(jang-syun-ming ko-chung-chi bao-tien-i li-lih-ping liu-ai-sen).in. and (treating treatment)	USPAT; US-PGPUB	2004/11/03 14:03
-	5	(jang-syun-ming ko-chung-chi bao-tien-i li-lih-ping liu-ai-sen).in. and ((treating treatment) same "SiOC")	USPAT; US-PGPUB	2004/10/28 10:36
-	264	((dielectric with (low adj1 K)) SiOC) with treat\$4.bi.	USPAT; US-PGPUB	2004/10/28 10:39
-	145	((dielectric with (low adj1 K)) SiOC) with treat\$4.bi.) and (dual adj1 damascene)	USPAT; US-PGPUB	2004/10/28 10:41
-	38	((dielectric with (low adj1 K)) SiOC) with treat\$4.bi.) and (dual adj1 damascene)) and ((hydrogen energy heat) adj1 treatment)	USPAT; US-PGPUB	2004/10/28 13:40
-	3	((carbon adj1 doped adj1 oxide) SiOC) same treatment same hard\$4.bi.	USPAT; US-PGPUB	2004/10/28 13:40
-	75	((carbon adj1 doped adj1 oxide) SiOC) same treatment.bi.	USPAT; US-PGPUB	2004/10/28 13:40
-	38	((dielectric with (low adj1 K)) SiOC) with treat\$4.bi.) and (dual adj1 damascene)) and ((hydrogen energy heat) adj1 treatment)	USPAT; US-PGPUB	2004/10/28 13:41
-	66	((carbon adj1 doped adj1 oxide) SiOC) same treatment.bi.) not (((dielectric with (low adj1 K)) SiOC) with treat\$4.bi.) and (dual adj1 damascene)) and ((hydrogen energy heat) adj1 treatment))	USPAT; US-PGPUB	2004/10/28 13:41
-	96	(method process) with attach\$3 with (electronic adj1 component).clm.	USPAT	2004/11/01 14:28
-	1	("6764946").PN.	USPAT; US-PGPUB	2004/11/03 10:31
-	3	(inductor same ((electroplat\$3 electrodeposit\$3 electroless) with resin with (conductor metal)) same electrode).bi.	USPAT; US-PGPUB	2004/11/03 10:34
-	432	(treat\$4 with (dielectric insulat\$3) with hard\$4).bi.	USPAT; US-PGPUB	2004/11/03 14:06
-	19	(treat\$4 with (dielectric insulat\$3) with (hard\$4 adj1 (layer film))).bi.	USPAT; US-PGPUB	2004/11/04 08:59